

Part Number	Customer
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Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.50 mm	
	2.0 Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none / semi std	
	5.0 Overall Thickness	511.00 +/- 26.10 μ m	ADE, 100%
	6.0 Total Thickness Variation (TTV)	<3.00 μ m	Guaranteed by Process
	7.0 Bow	<80.00 μ m	ADE to ASTM F534, 20%
	8.0 Warp	<80.00 μ m	ADE to ASTM F657, 20%
	9.0 Edge Chips	0	Bright Light, 100%
	10.0 Edge Exclusion	5mm	
	11.0 Bond Anneal cycle	>1000deg for 60mins	Guaranteed by process
HandleSilicon	12.0 Handle Growth Method	CZ	Wafer Vendor
	13.0 Handle Orientation	{100}+/-1 degree	Wafer Vendor
	14.0 Handle Thickness	500.00 +/- 25.00 μ m	ADE, 100%
	15.0 Handle Doping Type	N or P	Wafer Vendor
	16.0 Handle Dopant	Any	Wafer Vendor
	17.0 Handle Resistivity	>1 ohmem	Wafer Vendor
	18.0 Backside Finish	Lapped/Etched with oxide and lasermark	Wafer Vendor
BuriedOxide	19.0 Oxide Type	Thermal	
	20.0 Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0 Oxide formed on	Handle or/and device wafer	
DeviceSilicon	22.0 Device Growth Method	FZ	Wafer Vendor
	23.0 Device Orientation	{100}+/-1 degree	Wafer Vendor
	24.0 Nominal Thickness	10.00 +/- 1.00 μ m	100% 9-Pt (note3)
	25.0 Within Wafer Variation	TTV <2um. Per Device Silicon Nominal Thickness.	100% 9-pt (note3)
	26.0 Top surface Surface Average roughness, Ra	<0.5nm	Guaranteed by process
	27.0 Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	28.0 Device Doping Type	Intrinsic	Wafer Vendor
	29.0 Device Dopant	Any	Wafer Vendor
	30.0 Device Resistivity	>20000 ohmem	Wafer Vendor
	31.0 Voids	0	Bright Light, 100% (note 2)
	32.0 Scratches	0	Bright Light, 100% (note 2)
	33.0 Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information